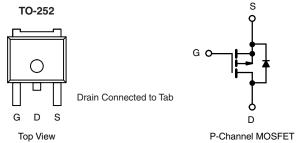


**Vishay Siliconix** 

# Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 60			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 \text{ V}$	0.055			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$	0.100			
I <sub>D</sub> (A)	- 20			
Configuration	Single			

#### TO-252



#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Package with Low Thermal Resistance
- 100 %  $R_{\rm q}$  and UIS Tested
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified<sup>d</sup>



ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD19P06-60L-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \text{ °C}$ , unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	- 60	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	- 20		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	- 11	А	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 25		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 80		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 24		
Single Pulse Avalanche Energy		E <sub>AS</sub>	28	mJ	
Maximum Dawar Dissinctionh	T <sub>C</sub> = 25 °C	D	46	w	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	P <sub>D</sub>	15		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	3.2	0/10	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static	•	-					•
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA		- 60	-	-	v
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1.5	-	- 2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 60 V	-	-	- 1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS}$ = - 60 V, $T_{J}$ = 125 °C	-	-	- 50	μA
		$V_{GS} = 0 V$	$V_{DS}$ = - 60 V, $T_{J}$ = 175 °C	-	-	- 150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le$ - 5 V	- 20	-	-	Α
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 19 A	-	0.046	0.055	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 19 A, T <sub>J</sub> = 125 °C	-	-	0.095	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 19 A, T <sub>J</sub> = 175 °C	-	-	0.125	Ω
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 10 A	-	0.075	0.100	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> =	- 15 V, I <sub>D</sub> = - 17 A	-	20	-	S
Dynamic <sup>b</sup>	•	-					1
Input Capacitance	C <sub>iss</sub>			-	1192	1490	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 25 V, f = 1 MHz	-	160	200	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	96	120	
Total Gate Charge <sup>c</sup>	Qg			-	27	41	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} = -30 \text{ V}, I_{D} = -19 \text{ A}$	-	3.9	- n(	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	5.9	-	1
Gate Resistance	Rg	f = 1 MHz		2.3	4.7	7.1	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	7	11	
Rise Time <sup>c</sup>	t <sub>r</sub>	$\label{eq:V_DD} \begin{array}{l} V_{\text{DD}} = -30 \; V, \; R_{\text{L}} = 1.6 \; \Omega \\ I_{\text{D}} \cong -19 \; A, \; V_{\text{GEN}} = -10 \; V, \; R_{\text{g}} = 1 \; \Omega \end{array}$		-	9	14	- ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	25	38	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	12	18	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>	•					
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 80	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = - 10 A, V <sub>GS</sub> = 0 V		-	- 0.85	- 1.5	V

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

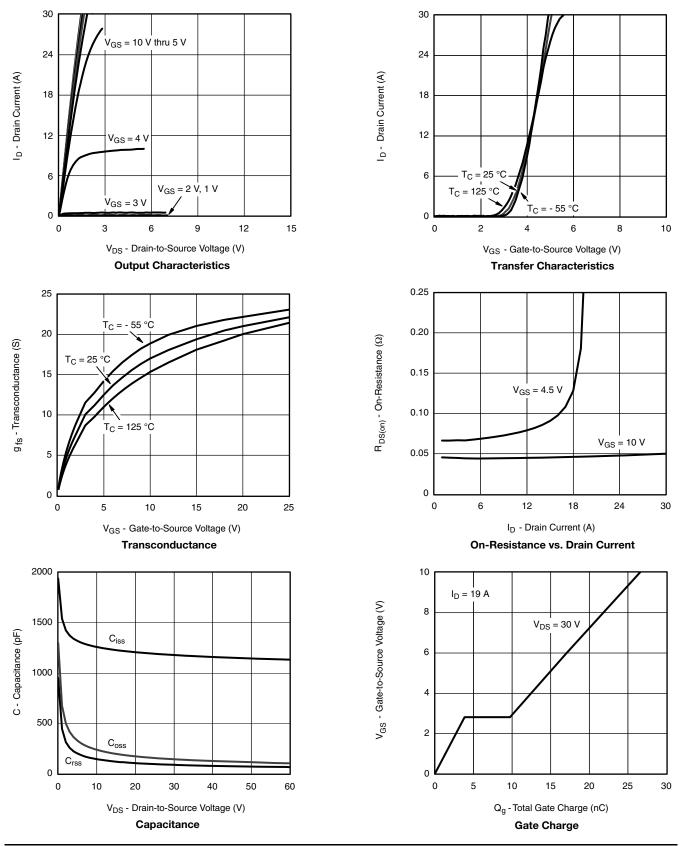
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



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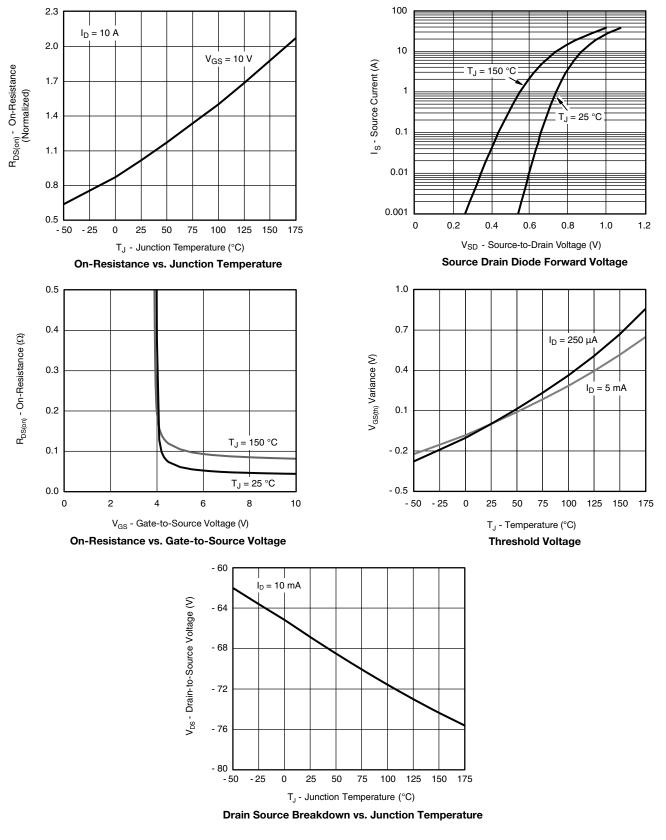
Document Number: 65158

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## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



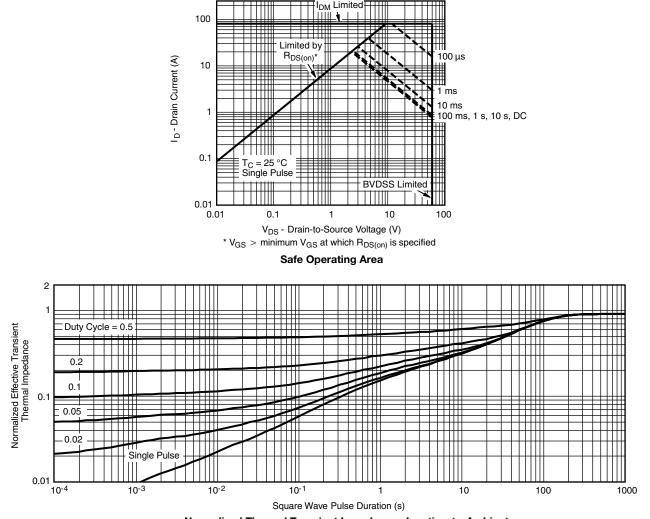
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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



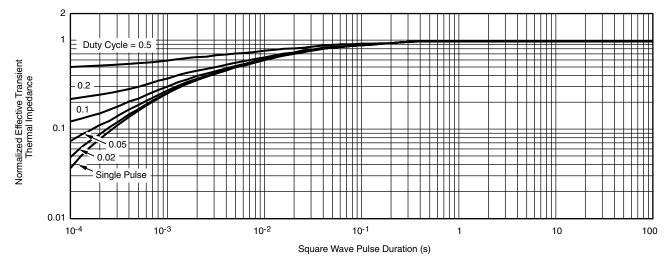
Normalized Thermal Transient Impedance, Junction-to-Ambient

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## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

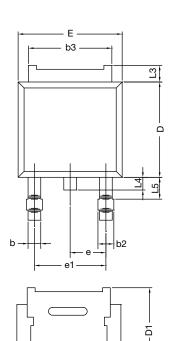
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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**TO-252AA** Case Outline

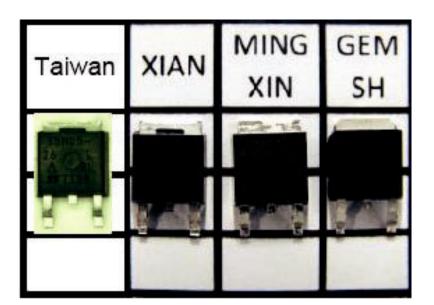
	MILLIN	<b>IETERS</b>	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0359-Rev. O, 03-Jun-13 DWG: 5347					

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Notes

• Dimension L3 is for reference only.

• Xi'an, Mingxin, and GEM SH actual photo.



Revision: 03-Jun-13

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#### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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